

# Wafer Tape Selection Analysis for Adhesion Problem Mitigation

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## ABSTRACT

Wafer passivation or the protective layer of the internal circuitry of the die plays a major role of providing protection and the isolation of electrical stability of the active circuit on the top area of the wafer. Passivation is normally a screen of an oxide layer on the surface of the silicon wafer or the carrier of internal circuitry of the die. Passivation is normally in the form of polyimide or a glass material. From the wafer structure, it is important to cover the active circuit to ensure no other noises will be induced to the wafer. Inclusion of the passivation layer will help maximize the functionality of the semiconductor device thus eliminating noises coming from the external sources.

As the integrated circuit (IC) package goes thinner, the requirement of having the active circuit or the die thinner is the main concern during the wafer preparation process. Wafer backgrinding or wafer thinning is the focal process involved to satisfy such requirement. Prior performing the wafer thinning process, the application of tape, normally in a form of polyolefin or polyvinyl chloride should be performed to eliminate contamination and protects the active layer of the wafer during the process. However, there should be enough adhesion between the wafer and the thinning tape itself. High adhesion strength may lead to adhesive remains or worst, passivation will be peeled off from the active layer of the wafer.

Adhesion to the passivation layer should be properly evaluated and monitored in such way that will eliminate adhesive remains during detaping process after wafer thinning. The effect of adhesion strength could be predicted by properly selecting thinning or protective tape to be used. Higher adhesion strength could be achieved but due to criticality of passivation to tape adhesion, ultra-violet (UV) process should be included to substantially decreased the adhesion. The importance of UV exposure is also discussed on this paper.

*Keywords:* Wafer tape; wafer preparation; pre-assembly; ultraviolet; passivation; adhesion.

## 1. INTRODUCTION

Wafer thinning is one of the critical pre assembly process in which wafers are grinded or thinned to a required thickness to cater the package requirements. However, it is important to protect the active layer of the wafer, thus applying an adhesive tape is a must. There should be no water penetration during the grinding or thinning process and no contamination on the thinning tape so that the active layer is totally intact after thinning process. In line with that, the protective tape should have three critical characteristics: Suitable adhesion, Easy de taping and good uniformity after thinning.

Different silicon technologies have been developed according to its application. Wafer could have different surface finish and the common is the application of a passivation layer. The peeling off of the wafer passivation together with the protective tape during detaping process

28 is one major concern. With this, the assembly manufacturing plant carefully analyzed the  
29 criticality of **tape adhesion**. Three (3) different **protective tapes** are evaluated and prudently  
30 select the suitable **protective tape** to this wafer technology. The evaluation will involve on  
31 how proper selection of the **protective tape** adhesion strength will eliminate wafer passivation  
32 removals.

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34 The importance of removing properly the protective tape is to ensure the workability and  
35 good response of the electrical performance of our integrated circuit manufacturing. Several  
36 problems may arise like broken dies, contamination, lifted wires and delamination that may  
37 cause malfunction of the integrated circuit. The study will help the practitioners of the  
38 integration circuit manufacturing to properly select protective tapes to eliminate problems  
39 during the wafer preparation process, specifically for wafer with passivation.

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## 41 **1.1 Wafer Passivation**

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43 Wafer passivation is normally the masking of an oxide layer on the surface of the active layer  
44 of the wafer. Passivation is important to provide electrical stability and insulation to the  
45 environment. There are two common forms of passivation which are polyimides and silicate  
46 glass. Though on the specific silicon wafer technology has been developed polyimide resin  
47 is used.

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49 Polyimides are a polymer of imide monomers [1], normally on orange or yellow color  
50 appearance. Exceptional characteristics of polyimides are thermal stability, good chemical  
51 resistance, and excellent mechanical properties. Polyimides have good mechanical  
52 elongation and tensile strength. The polyimide layers have good mechanical elongation and  
53 tensile strength, which helps provide good adhesion of the deposited metal layer to the  
54 polyimide. The minimal interaction of the polyimide and the deposited metal and the thermal  
55 stability helps provide good and reliable insulation of the wafer to the environmental stresses  
56 [2]. Normally in the wafer fabrication process, passivation is placed on the top surface of the  
57 silicon wafer as shown in Fig. 1.

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Fig. 1. Wafer structure cross-sectional view

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## 63 **1.2 Wafer Tape**

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65 Prior wafer thinning, taping the active circuit of wafer is necessary. **Protective tape** would  
66 help eliminate water penetration, breakage or cushioning adsorbs during **thinning process**  
67 and maintains uniformity after **thinning**, which have been verified by TTV (Total Thickness  
68 Variation). TTV is the characteristics measured to differentiate the thickness within a wafer  
69 and compared to another wafer. After thinning, **protective tape** would be de taped and there  
70 should be no wafer breakage and no contamination due to adhesive material. In with all  
71 these requirements and as final wafer thickness goes thinner; two types of **protective tape** in  
72 Fig. 2 are derived: conventional Non-UV type and UV curable type.

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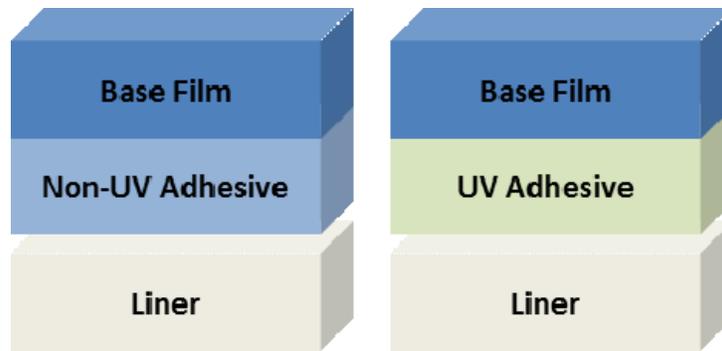


Fig. 2. Graphical representation of types of protective tape

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Conventional protective tapes have normally a much lower adhesion strength compared to UV type tapes. Hence, a little contamination could be transferred to the wafer surface. On the other hand, UV type tapes show no water penetration and wafer breakage during thinning due to its higher adhesion strength compared to conventional types. Also, UV type tape requires additional exposure to ultra violet radiation that will help reduce its adhesion strength, will therefore aid the ease of detaping process. Due to peeling off of passivation from the active circuit of the wafer, three different protective tapes have been selected to check different responses during detaping process.

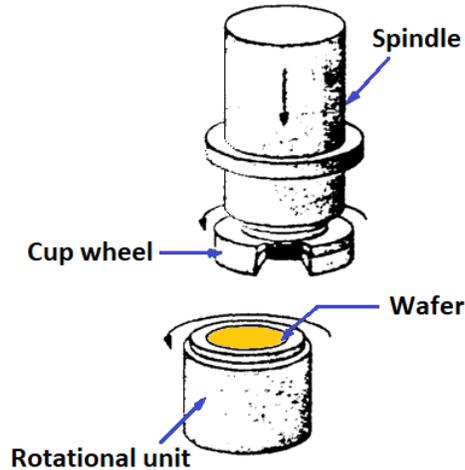
## 2. LITERATURE REVIEW

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Wafer thinning is the thinning of semiconductor wafers by removing material from the unpolished wafer back side. Wafers are often fabricated thicker than necessary, normally at 600 to 750µm thick, and this has been determined by the stresses during processing and the requirement of handling robustness. During the back end process, there is a need for thinning the wafers in order to meet the package requirements and at the same time, the functionality of the IC package [3-5]. In connection, most of IC assembly wafer thickness is reduced to around 50% thinner, partly for mechanical reasons and improve thermal transfer [4-6].

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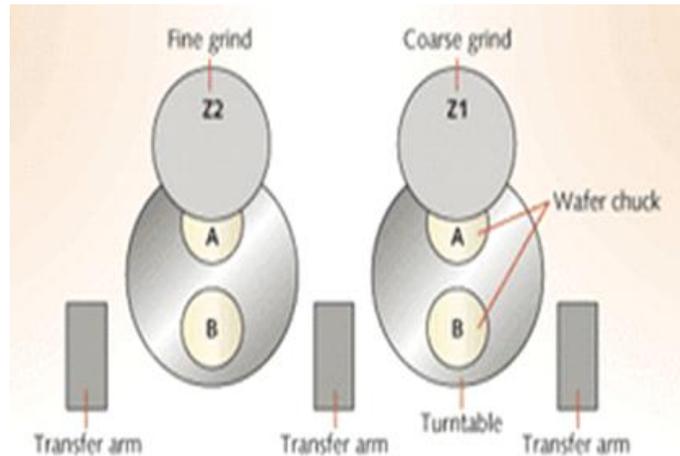
There are several methods that are presently being used for thinning wafers; the most popular is the well-established mechanical thinning and polishing technique. As illustrated in Fig. 4, a standard wafer thinner has a rotating work chuck table wherein the wafer or the work piece is being positioned; diagonally a spindle will help the rotating diamond cup wheel turn towards the chuck table [6-7]. The downward movement of the spindle carrying the cup wheel removes silicon material from the surface of the wafer, thus creating a flat surface. The wheel alignment and chuck table planarity plays a major role on attaining uniformity of wafer thickness. However, it is difficult to measure this setting so post-thinning measurements are made using a non-contact capacitive probe. The parameter normally assessed is total thickness variation (TTV), where a typical target value is <10µm.



**Fig. 3. Schematic of a rotational wafer thinner.**

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As of today, thinning machines are using a multi-step thinning operation. The typical two-step wafer thinning shown in Fig. 4 is using the two separate spindles and chuck tables. The operation will involve a thinning using a large grit diamond wheel (Z1) that will coarsely grind or thin the wafer while the second process using a finer grit (Z2) will thin the wafer to its final thickness precisely. The large grit diamond wheel removes approximately 90 percent of the excess material. While the fine grit is responsible for attaining the final thickness with a smoother silicon back side finish.



**Fig. 4. Two-step wafer thinning process**

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After thinning process, the protective tape should be removed in preparation for the wafer sawing. There should be no adhesive residuals that may lead to wafer surface contamination. Therefore, an extensive evaluation should be performed to suitably select the protective tape that will surpass all wafer preparation requirements, specifically adhesion strength that will eliminate surface contamination, ease of detaping and will not incur wafer breakage.

132 **3. EXPERIMENTATION**

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134 **3.1 Protective Tape Selection**

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136 Wafer with polyimide passivation, on a 200mm diameter Complementary metal-oxide-  
137 semiconductor or CMOS Silicon technology outline, have been used to evaluate and select  
138 appropriate Protective tape to eliminate detachment of the wafer passivation after de taping  
139 process. All 3 wafers are all received with 725µm wafer thickness will be thinned on the  
140 same final thickness of 105µm. Also, same machine is used, with installed UV curing and de  
141 taping process up to wafer mounting, for all the three evaluation wafers. The thinning  
142 machine have also same machine setting of same mounting and detaping chuck table  
143 temperature of 33.5 ± 5°C and 40-50°C respectively, across the evaluation.

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145 Three different thinning tapes presented in Table 1 have been selected to appropriately  
146 evaluate the best eliminator of peeling issue of the passivation from the active layer of the  
147 wafer. The first protective tape is on a conventional type and been used on the released  
148 process for complementary metal-oxide semiconductor (CMOS) wafers. Adhesion strength  
149 of the conventional type is compared lower than the two other protective tape. The other 2  
150 types are both on UV type protective tape, which differs on adhesion strength ratio (before  
151 and after UV) but almost on the same total and adhesive thickness. UV Tape 1 is designed  
152 to have higher adhesion strength before UV but a lower adhesion after UV.

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154 **Table 1. Protective tape configuration**

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Specification	Unit	Conventional	UV Tape 1	UV Tape 2
Total thickness	µm	180	135	120
Adhesive thickness	µm	65	35	40
Adhesion strength	Before UV	N/20m m	25.33	7.84
	After UV		0.04	0.16

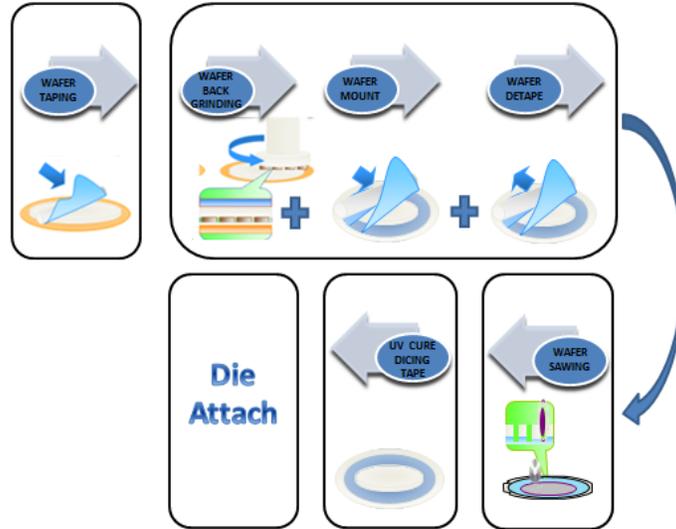
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157 **3.2 Process Flow**

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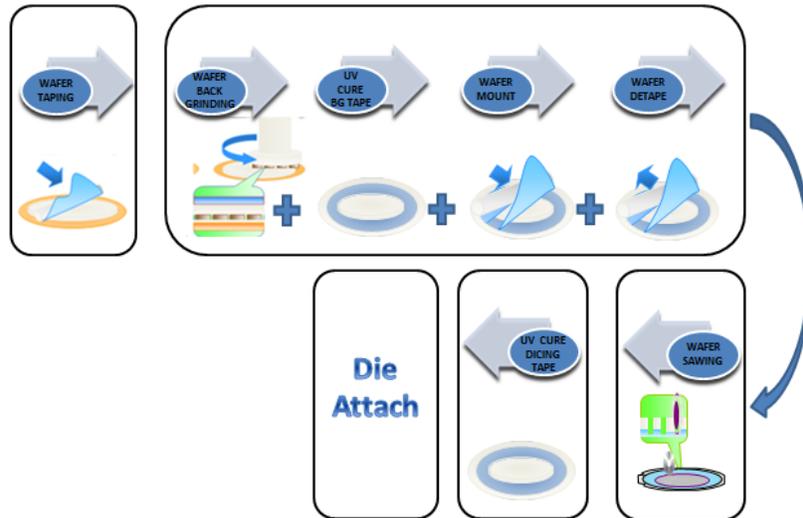
159 The evaluation of the three wafers were processed on a single thinning machine with  
160 equipped UV curing and de taping process. The evaluation has been sub divided into two  
161 processes. The first process in Fig. 5 involves the procedure of normal thinning – detaping  
162 process flow with conventional tape type as protective tape. Another process show in Fig. 6  
163 involves the activation of UV curing after thinning. This will lessen the adhesion strength of  
164 the two UV curable type of protective tape prior detaping process. The result will be  
165 determined by process elimination and be based according to the visual inspection criteria.

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Fig. 5. Pre-assembly process flow for **conventional protective tape**



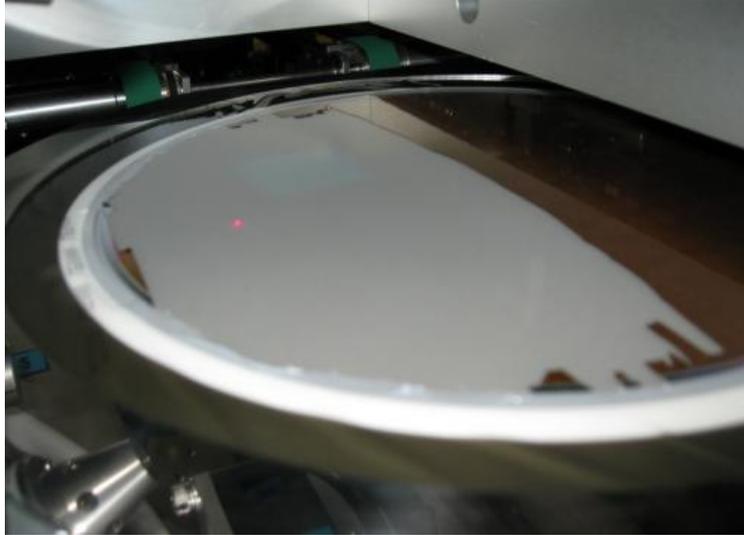
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Fig. 6. Pre-assembly process flow for UV-curable **protective tape**

## 4. RESULTS AND DISCUSSION

### 4.1 Conventional Type **Protective Tape**

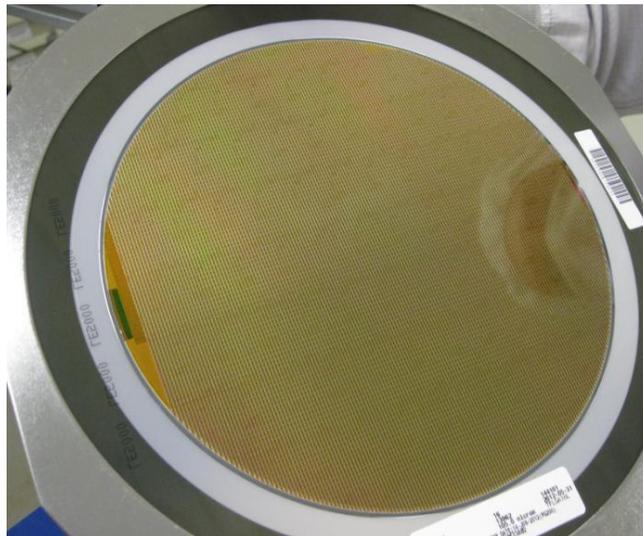
Conventional type **protective tape** encountered broken wafer or detachment of the passivation layer after detaping as depicted in Fig. 7. Therefore, the amount of adhesion strength at 1.47 N/20mm is too sticky for the polyimide and thinning tape.



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185 **Fig. 7. Detachment of the passivation layer after wafer detaping**  
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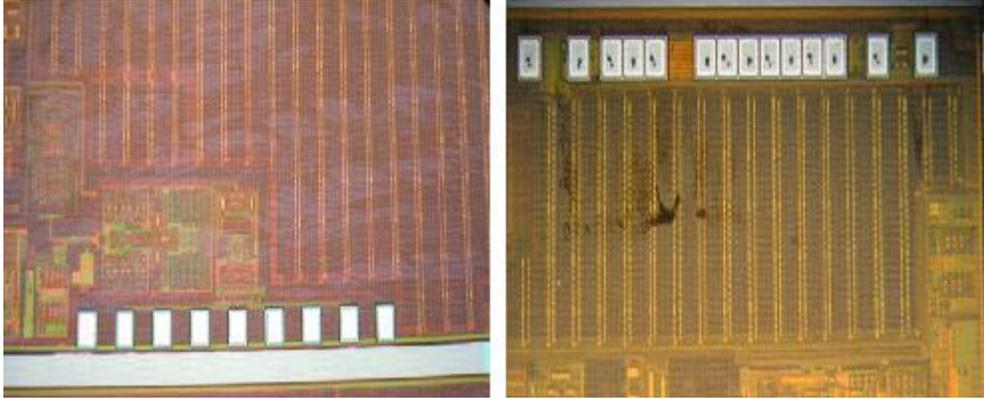
187 **4.2 UV-Curable Type Protective Tape**  
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189 The two UV curable types are processed on same process flow with the activation of UV  
190 curing after thinning. UV type 1 having higher adhesion strength during thinning and a much  
191 lower adhesion after UV curing have not encountered peeling of the passivation in Fig. 8.  
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195 **Fig. 8. Actual wafer after detaping process**  
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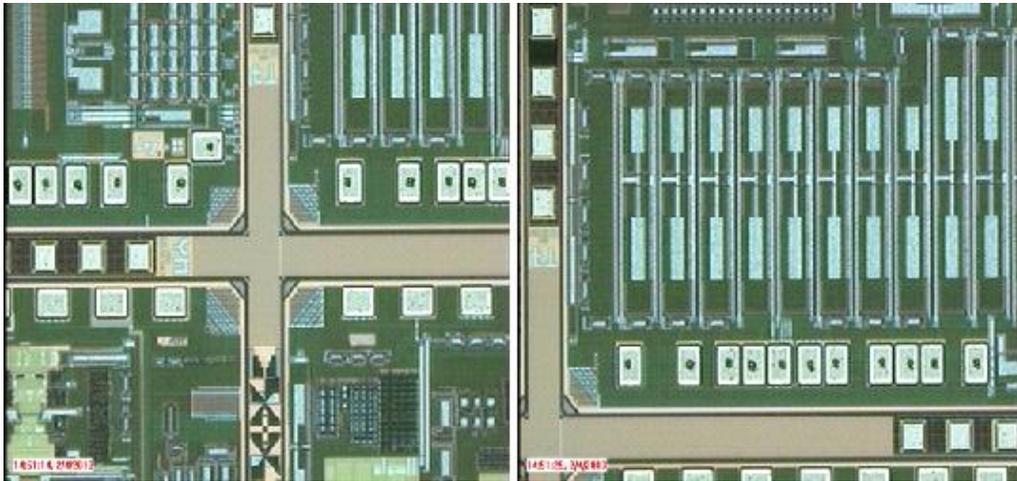
197 Meanwhile, adhesive remains/contamination on the passivation surface as well as on the  
198 bond pad was observed during the inspection using a high magnification microscope in Fig.  
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**Fig. 9. Contamination after wafer thinning**

The affected wafer was continuously processed until wafer saw process but still adhesive/contamination is present on the passivation surface after wafer sawing. On the other hand, UV type 2, with higher adhesion strength after the UV exposure and lower adhesion before UV, showed good response after detaping process. As a result, there is none anomaly or adhesive contamination found in Fig. 10 on the passivation and even on the bond pad.



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**Fig. 10. No adhesive contamination after detaping process**

## 5. CONCLUSION AND RECOMMENDATIONS

Based on the evaluation, Conventional type protective tape will aggravate the peeling off of the passivation from the active layer of the wafer. However, UV type protective tapes will eliminate such peeling problem of the passivation by lower adhesion strength after UV exposure.

Lower adhesion strength before UV exposure and higher adhesion after UV greatly helped to mitigate the peeling off problem of passivation from the active layer after detaping. Hence,

226 maintaining low adhesion strength of the UV curable type **protective tapes**, both before and  
227 after UV exposure, will also eliminate adhesive remains after detaping process.

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229 Based on the results, it is highly recommended to use a UV-curable type **protective tape** on  
230 a polyimide based passivation to eliminate detachment of the passivation after detaping  
231 process. It is also important to have the proper selection of the appropriate **protective tape**  
232 to be used and this involves carefully understanding the adhesion strength ratio between  
233 before and after UV exposure.

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235 For further improvement, it is highly recommended to use high vacuum efficient chuck table  
236 to properly handle incoming wafer warpage and ensure good flattening on the chuck table  
237 and eliminating the possibility of inferior **grinding or thinning**. Redesign of special robot arms  
238 should also be considered to eliminate the possibility of wafer breakage when handling or  
239 unloading thinner wafers after **thinning**, or use **an inline wafer preparation system**. Moreover,  
240 a special process should be considered wherein making an outer circumference lip, where  
241 no **thinning** pressure is applied on the edge of the wafer during **thinning**. For ensuing critical  
242 processes like that of the wafer saw, discussions in **[5,8-9]** are helpful to prevent or eliminate  
243 defects related to wafer preparation. Furthermore, it is highly important that the assembly  
244 manufacturing processes ensure appropriate ESD checks and controls. Learnings shared in  
245 **[10]** are very helpful to realize proper and effective ESD-related controls.

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